Oleg Evgenevich Tereshchenko

List of Publications by Year in Descending Order

166 papers	2,479 citations	27 h-index	41 g-index
175 ext. papers	2,872 ext. citations	4 avg, IF	4.7 L-index

#	Paper	IF	Citations
166	Modulation of the Dirac Point Band Gap in the Antiferromagnetic Topological Insulator MnBi2Te4 due to the Surface Potential Gradient Change. *Journal of Experimental and Theoretical Physics*, **2022**, 134, 103-111	1	2
165	Electronic Structure of Magnetic Topological Insulators Mn(Bi1 xSbx)2Te4 with Various Concentration of Sb Atoms. *JETP Letters*, **2022**, 115, 286-291	1.2	1
164	Structural Characterization of Pb0.7Sn0.3Te Crystalline Topological Insulator Thin Films Grown on Si(111). *Semiconductors*, **2021**, 55, 682	0.7	
163	Non-monotonic variation of the Kramers point band gap with increasing magnetic doping in BiTeI. *Scientific Reports*, **2021**, 11, 23332	4.9	2
162	PHOTOEMISSION PROPERTIES OF THE MULTIALKALI PHOTOCATHODE. *Avtometriya*, **2021**, 57, 70-76	1.5	
161	A new imaging concept in spin polarimetry based on the spin-filter effect. *Journal of Synchrotron Radiation*, **2021**, 28, 864-875	2.4	3
160	Profiling spin and orbital texture of a topological insulator in full momentum space. *Physical Review B*, **2021**, 103,	3.3	2
159	Optical Phonon Spectrum of the Ge2Sb2Te5 Single Crystal. *JETP Letters*, **2021**, 113, 651-656	1.2	0
158	Tunable non-integer high-harmonic generation in a topological insulator. *Nature*, **2021**, 593, 385-390	50.4	19
157	Growth of Bi2Se3/graphene heterostructures with the room temperature high carrier mobility. *Journal of Materials Science*, **2021**, 56, 9330-9343	4.3	3
156	Photoemission Properties of a Multialkali Photocathode. *Optoelectronics, Instrumentation and Data Processing*, **2021**, 57, 505-510	0.6	0
155	Band gap opening in the BiSbTeSe2 topological surface state induced by ferromagnetic surface reordering. *Physical Review Materials*, **2021**, 5,	3.2	1
154	Preparation of Atomically Clean and Structurally Ordered Surfaces of Epitaxial CdTe Films for Subsequent Epitaxy. *Semiconductors*, **2021**, 55, S62-S66	0.7	0
153	Origin of Degradation of the CaF2/BaF2 Buffer Layers on Si(111). *Doklady Physics*, **2020**, 65, 15-17	0.8	2
152	Electrically Controlled Spin Injection from Giant Rashba Spin-Orbit Conductor BiTeBr. *Nano Letters*, **2020**, 20, 4782-4791	11.5	11
151	Features of MIS Structures Based on Insulating PbSnTe:In Films with the Composition in the Vicinity of the Band Inversion Related to Their Ferroelectric Properties. *Semiconductors*, **2020**, 54, 1325-1331	0.7	
150	Vapor growth of Bi2Se3 and Bi2O2Se crystals on mica. *Materials Research Bulletin*, **2020**, 129, 110906	5.1	0

149	Field Effect and Spin-Valve Effect in the PbSnTe Topological Crystalline Insulator. *Optoelectronics, Instrumentation and Data Processing*, **2020**, 56, 553-557	0.6	4
148	Change of the topological surface states induced by ferromagnetic metals deposited on BiSbTeSe2. *Journal of Physics: Conference Series*, **2020**, 1697, 012095	0.3	
147	Electrochemically exfoliated thin BiSe films and van der Waals heterostructures BiSe/graphene. *Nanotechnology*, **2020**, 31, 125602	3.4	2
146	Optical and Transport Properties of Epitaxial Pb0.74Sn0.26Te(In) Films with a Modifiable Surface. *Semiconductors*, **2020**, 54, 1086-1091	0.7	
145	Energy-Gap Opening Near the Dirac Point after the Deposition of Cobalt on the (0001) Surface of the Topological Insulator BiSbTeSe2. *Semiconductors*, **2020**, 54, 1051-1055	0.7	3
144	Sign-Alternating Photoconductivity in PbSnTe:In Films in the Space-Charge-Limited Current Regime. *Semiconductors*, **2020**, 54, 951-955	0.7	0
143	Spectral detection of spin-polarized ultra low-energy electrons in semiconductor heterostructures. *Ultramicroscopy*, **2020**, 218, 113076	3.1	3
142	Structure and magneto-electric properties of Co-based ferromagnetic films grown on the Pb0.71Sn0.29Te crystalline topological insulator. *Materials Chemistry and Physics*, **2020**, 240, 122134	4.4	6
141	Magnetic and Electronic Properties of Gd-Doped Topological Insulator Bi1.09Gd0.06Sb0.85Te3. *Journal of Experimental and Theoretical Physics*, **2019**, 129, 404-412	1	9
140	Electronic correlation determining correlated plasmons in Sb-doped Bi2Se3. *Physical Review B*, **2019**, 100,	3.3	3
139	Features of the Impurity-Photoconductivity Spectra of PbSnTe(In) Epitaxial Films with Temperature Changes. *Semiconductors*, **2019**, 53, 1272-1277	0.7	1
138	Surface ▯nductivity Dynamics in PbSnTe:In Films in the Vicinity of a Band Inversion. *Semiconductors*, **2019**, 53, 1182-1186	0.7	2
137	Inverted Dirac-electron population for broadband lasing in a thermally activated p-type topological insulator. *Physical Review B*, **2019**, 99,	3.3	3
136	Dirac gap opening and Dirac-fermion-mediated magnetic coupling in antiferromagnetic Gd-doped topological insulators and their manipulation by synchrotron radiation. *Scientific Reports*, **2019**, 9, 4813	4.9	16
135	Magnetic-impurity-induced modifications to ultrafast carrier dynamics in the ferromagnetic topological insulators Sb2▯ V x Te3. *New Journal of Physics*, **2019**, 21, 093006	2.9	5
134	Bidirectional surface photovoltage on a topological insulator. *Physical Review B*, **2019**, 100,	3.3	2
133	Modification of the Surface Properties of PbSnTe<In> Epitaxial Layers with Composition near Band Inversion. *Technical Physics*, **2019**, 64, 1704-1708	0.5	4
132	Structural and vibrational properties of PVT grown BiTeCl microcrystals. *Materials Research Express*, **2019**, 6, 045912	1.7	8

131	Ultrafast dynamics of an unoccupied surface resonance state in Bi2Te2Se. *Physical Review B*, **2018**, 97,	3.3	4
130	Systematics of electronic and magnetic properties in the transition metal doped Sb2Te3 quantum anomalous Hall platform. *Physical Review B*, **2018**, 97,	3.3	32
129	A Study of the Crystal Structure of Co40Fe40B20 Epitaxial Films on a Bi2Te3 Topological Insulator. *Technical Physics Letters*, **2018**, 44, 184-186	0.7	5
128	Spin and electronic structure of the topological insulator Bi1.5Sb0.5Te1.8Se1.2. *Materials Chemistry and Physics*, **2018**, 207, 253-258	4.4	2
127	Influence of quantizing magnetic field and Rashba effect on indium arsenide metal-oxide-semiconductor structure accumulation capacitance. *Journal of Applied Physics*, **2018**, 123, 173901	2.5	
126	Landau Level Broadening in the Three-Dimensional Topological Insulator Sb2Te3. *Physica Status Solidi - Rapid Research Letters*, **2018**, 12, 1800112	2.5	1
125	Gigantic 2D laser-induced photovoltaic effect in magnetically doped topological insulators for surface zero-bias spin-polarized current generation. *2D Materials*, **2018**, 5, 015015	5.9	3
124	Crystalline structure and magnetic properties of structurally ordered cobalt–iron alloys grown on Bi-containing topological insulators and systems with giant Rashba splitting. *CrystEngComm*, **2018**, 20, 3419-3427	3.3	10
123	Electronic and spin structure of the wide-band-gap topological insulator: Nearly stoichiometric Bi2Te2S. *Physical Review B*, **2018**, 97,	3.3	11
122	Dirac cone intensity asymmetry and surface magnetic field in V-doped and pristine topological insulators generated by synchrotron and laser radiation. *Scientific Reports*, **2018**, 8, 6544	4.9	8
121	Impact of Ultrathin Pb Films on the Topological Surface and Quantum-Well States of Bi2Se3 and Sb2Te3 Topological Insulators. *Journal of Experimental and Theoretical Physics*, **2018**, 126, 535-540	1	1
120	Signatures of in-plane and out-of-plane magnetization generated by synchrotron radiation in magnetically doped and pristine topological insulators. *Physical Review B*, **2018**, 97,	3.3	12
119	Enhanced surface state protection and band gap in the topological insulator PbBi4Te4S3. *Physical Review Materials*, **2018**, 2,	3.2	4
118	CH3NH3PbI3 crystal growth, structure and composition. *Journal of Physics: Conference Series*, **2018**, 1124, 041008	0.3	2
117	Subcycle observation of lightwave-driven Dirac currents in a topological surface band. *Nature*, **2018** , 562, 396-400	50.4	83
116	Origin of spin-polarized photocurrents in the topological surface states of Bi2Se3. *Physical Review B* , **2018**, 98,	3.3	6
115	Anomalous Behavior of the Elastic and Optical Properties in Bi1.5Sb0.5Te1.8Se1.2 Topological Insulator Induced by Point Defects. *Physica Status Solidi (B): Basic Research*, **2018**, 255, 1800264	1.3	2
114	Topological states induced by local structural modification of the polar BiTeI(0001) surface. *New Journal of Physics*, **2018**, 20, 063035	2.9	3

113	Enhanced photovoltage on the surface of topological insulator via optical aging. *Applied Physics Letters*, **2018**, 112, 192104	3.4	8
112	Shubnikov-de Haas oscillations in p and n-type topological insulator (Bi Sb)Te. *Journal of Physics Condensed Matter*, **2018**, 30, 265001	1.8	5
111	Anomalously large gap and induced out-of-plane spin polarization in magnetically doped 2D Rashba system: V-doped BiTeI. *2D Materials*, **2017**, 4, 025055	5.9	9
110	Spin-resolved band structure of heterojunction Bi-bilayer/3D topological insulator in the quantum dimension regime in annealed BiTeSe. *Scientific Reports*, **2017**, 7, 45797	4.9	8
109	AlN/GaN heterostructures for normally-off transistors. *Semiconductors*, **2017**, 51, 379-386	0.7	4
108	Prolonged duration of nonequilibrated Dirac fermions in neutral topological insulators. *Scientific Reports*, **2017**, 7, 14080	4.9	18
107	Photoemission and Injection Properties of a Vacuum Photodiode with Two Negative-Electron-Affinity Semiconductor Electrodes. *Physical Review Applied*, **2017**, 8,	4.3	5
106	Geometric and electronic structure of the Cs-doped Bi2Se3(0001) surface. *Physical Review B*, **2017**, 95,	3.3	5
105	Ultrafast energy- and momentum-resolved surface Dirac photocurrents in the topological insulator Sb2Te3. *Physical Review B*, **2017**, 95,	3.3	25
104	Conductance oscillations and zero-bias anomaly in a single superconducting junction to a three-dimensional Bi 2 Te 3 topological insulator. *Europhysics Letters*, **2017**, 119, 57009	1.6	6
103	Solar energy converters based on multi-junction photoemission solar cells. *Scientific Reports*, **2017**, 7, 16154	4.9	8
102	Giant Magnetic Band Gap in the Rashba-Split Surface State of Vanadium-Doped BiTeI: A Combined Photoemission and Ab Initio Study. *Scientific Reports*, **2017**, 7, 3353	4.9	11
101	Properties of methylammonium lead iodide perovskite single crystals. *Journal of Structural Chemistry*, **2017**, 58, 1567-1572	0.9	3
100	Crystal growth of Bi2Te3 and noble cleaved (0001) surface properties. *Journal of Solid State Chemistry*, **2016**, 236, 203-208	3.3	17
99	Superparamagnetism-induced mesoscopic electron focusing in topological insulators. *Physical Review B*, **2016**, 94,	3.3	9
98	Surface spin-polarized currents generated in topological insulators by circularly polarized synchrotron radiation and their photoelectron spectroscopy indication. *Physics of the Solid State*, **2016**, 58, 1675-1686	0.8	14
97	Optical properties and electronic structure of BiTeCl and BiTeBr compounds. *Optics and Spectroscopy (English Translation of Optika I Spektroskopiya)*, **2016**, 121, 364-370	0.7	7
96	Photoelectron spin polarization in the Bi2Te3(0001) topological insulator: Initial- and final-state effects in the photoemission process. *Physical Review B*, **2016**, 93,	3.3	10

95	Energetic and Spatial Mapping of Resonant Electronic Excitations. *Journal of Physical Chemistry C*, **2016**, 120, 13843-13849	3.8	7
94	Dual nature of magnetic dopants and competing trends in topological insulators. *Nature Communications*, **2016**, 7, 12027	17.4	61
93	Spin-texture inversion in the giant Rashba semiconductor BiTeI. *Nature Communications*, **2016**, 7, 11621	17.4	52
92	Scattering properties of the three-dimensional topological insulator Sb2Te3: Coexistence of topologically trivial and nontrivial surface states with opposite spin-momentum helicity. *Physical Review B*, **2016**, 93,	3.3	9
91	Plasma-Wave Terahertz Detection Mediated by Topological Insulators Surface States. *Nano Letters*, **2016**, 16, 80-7	11.5	99
90	Experimental Realization of a Topological p-n Junction by Intrinsic Defect Grading. *Advanced Materials*, **2016**, 28, 2183-8	24	33
89	Out-of-plane polarization induced in magnetically-doped topological insulator Bi1.37V0.03Sb0.6Te2Se by circularly polarized synchrotron radiation above a Curie temperature. *Applied Physics Letters*, **2016**, 109, 222404	3.4	12
88	Specific features of the electronic, spin, and atomic structures of a topological insulator Bi2Te2.4Se0.6. *Physics of the Solid State*, **2016**, 58, 779-787	0.8	5
87	Mapping the effect of defect-induced strain disorder on the Dirac states of topological insulators. *Physical Review B*, **2016**, 94,	3.3	8
86	Single Electron Gating of Topological Insulators. *Advanced Materials*, **2016**, 28, 10073-10078	24	7
85	Role of anisotropy and spin-orbit interaction in the optical and dielectric properties of BiTeI and BiTeCl compounds. *JETP Letters*, **2015**, 101, 507-512	1.2	9
84	Systematics of molecular self-assembled networks at topological insulators surfaces. *Nano Letters*, **2015**, 15, 2442-7	11.5	31
83	Termination-dependent surface properties in the giant-Rashba semiconductors BiTeX (X=Cl, Br, I). *Physical Review B*, **2015**, 92,	3.3	19
82	InAs-based metal-oxide-semiconductor structure formation in low-energy Townsend discharge. *Applied Physics Letters*, **2015**, 107, 173501	3.4	14
81	Ferromagnetic HfO2/Si/GaAs interface for spin-polarimetry applications. *Applied Physics Letters*, **2015**, 107, 123506	3.4	5
80	The Peculiarities of Halogens Adsorption on A3B5(001) Surface. *IOP Conference Series: Materials Science and Engineering*, **2015**, 77, 012002	0.4	3
79	Direct measurement of the bulk spin structure of noncentrosymmetric BiTeCl. *Physical Review B*, **2015**, 91,	3.3	11
78	Early Stages of Halogen Adsorption on Cation-Rich InAs(001): Surface Etching Mechanism. *Journal of Physical Chemistry C*, **2014**, 118, 10097-10105	3.8	10

77	Melt growth of bulk Bi2Te3 crystals with a natural p□ junction. *CrystEngComm*, **2014**, 16, 581-584	3.3	43
76	Signatures of Dirac fermion-mediated magnetic order. *Nature Communications*, **2014**, 5, 5349	17.4	60
75	Defect and structural imperfection effects on the electronic properties of BiTeI surfaces. *New Journal of Physics*, **2014**, 16, 075013	2.9	20
74	Tuning the Dirac point position in Bi(2)Se(3)(0001) via surface carbon doping. *Physical Review Letters*, **2014**, 113, 116802	7.4	40
73	The gigantic Rashba effect of surface states energetically buried in the topological insulator Bi2Te2Se. *New Journal of Physics*, **2014**, 16, 065016	2.9	10
72	Probing the electronic properties of individual MnPc molecules coupled to topological states. *Nano Letters*, **2014**, 14, 5092-6	11.5	30
71	Electron dynamics of unoccupied states in topological insulators. *Journal of Electron Spectroscopy and Related Phenomena*, **2014**, 195, 258-262	1.7	20
70	Optical properties of BiTeI semiconductor with a strong Rashba spin-orbit interaction. *Optics and Spectroscopy (English Translation of Optika I Spektroskopiya)*, **2014**, 117, 764-768	0.7	7
69	Oxide-free InAs(111)A interface in metal-oxide-semiconductor structure with very low density of states prepared by anodic oxidation. *Applied Physics Letters*, **2014**, 105, 161601	3.4	12
68	Optical detection of spin-filter effect for electron spin polarimetry. *Applied Physics Letters*, **2014**, 105, 052402	3.4	12
67	Dynamics of the BiTeI lattice at high pressures. *JETP Letters*, **2014**, 98, 557-561	1.2	17
66	Electronic and spin structure of the topological insulator Bi2Te2.4Se0.6. *Physical Review B*, **2014**, 89,	3.3	32
65	Effect of fluorine on the electrical properties of anodic oxide/InAs(111)A interface. *Semiconductors*, **2014**, 48, 307-311	0.7	4
64	Study of the morphology and optical properties of anodic oxide layers on InAs (111)III. *Semiconductors*, **2013**, 47, 555-560	0.7	1
63	Unoccupied topological surface state in Bi2Te2Se. *Physical Review B*, **2013**, 88,	3.3	19
62	Visualizing spin-dependent bulk scattering and breakdown of the linear dispersion relation in Bi2Te3. *Physical Review B*, **2013**, 88,	3.3	33
61	Circular dichroism and superdiffusive transport at the surface of BiTeI. *Physical Review Letters*, **2013**, 111, 126603	7.4	10
60	Snapshots of Dirac fermions near the Dirac point in topological insulators. *Nano Letters*, **2013**, 13, 5797-802	11.5	62

59	Backward Reconstructions on GaAs(001) Surface Induced by Atomic Hydrogen Reactions: Surfactant-Assisted Low-Temperature Surface Ordering. *Journal of Physical Chemistry C*, **2013**, 117, 9723-9733	3.8	5
58	Bulk and surface Rashba splitting in single termination BiTeCl. *New Journal of Physics*, **2013**, 15, 085022	2.9	50
57	Ab-initio study of new Ga-rich GaAs(001) surface (4□) reconstruction. *Surface Science*, **2013**, 615, 97-102	1.8	5
56	Formation of anodic layers on InAs (111)III. Study of the chemical composition. *Semiconductors*, **2012**, 46, 552-558	0.7	9
55	Forming interface in Pd/Fe/GaAs/InGaAs structure for optical detector of free-electron spin. *Technical Physics Letters*, **2012**, 38, 12-16	0.7	2
54	Inertness and degradation of (0001) surface of Bi2Se3 topological insulator. *Journal of Applied Physics*, **2012**, 112, 113702	2.5	53
53	Unoccupied topological states on bismuth chalcogenides. *Physical Review B*, **2012**, 86,	3.3	54
52	Lattice dynamics of bismuth tellurohalides. *Physical Review B*, **2012**, 86,	3.3	31
51	Quick ellipsometric technique for determining the thicknesses and optical constant profiles of Fe/SiO2/Si(100) nanostructures during growth. *Technical Physics*, **2012**, 57, 1225-1229	0.5	8
50	Topological surface states with persistent high spin polarization across the Dirac point in Bi2Te2Se and Bi2Se2Te. *Physical Review Letters*, **2012**, 109, 166802	7.4	77
49	Etching or Stabilization of GaAs(001) under Alkali and Halogen Adsorption. *Journal of Physical Chemistry C*, **2012**, 116, 8535-8540	3.8	10
48	Vibrations in binary and ternary topological insulators: First-principles calculations and Raman spectroscopy measurements. *Physical Review B*, **2012**, 86,	3.3	68
47	Change in the electronic properties of an InAs (111)A surface at oxygen and fluorine adsorption. *Semiconductors*, **2012**, 46, 49-55	0.7	8
46	Chemistry of Wet Treatment of GaAs(111)B and GaAs(111)A in Hydrazine-Sulfide Solutions. *Journal of the Electrochemical Society*, **2011**, 158, D127	3.9	15
45	Formation of Inert Bi2Se3(0001) Cleaved Surface. *Crystal Growth and Design*, **2011**, 11, 5507-5514	3.5	97
44	Transport and magnetic properties of Fe/GaAs Schottky junctions for spin polarimetry applications. *Journal of Applied Physics*, **2011**, 109, 113708	2.5	11
43	Surfactant properties of cesium in molecular beam epitaxy of GaAs(100). *JETP Letters*, **2011**, 93, 585-590	1.2	
42	Stability of the (0001) surface of the Bi2Se3 topological insulator. *JETP Letters*, **2011**, 94, 465-468	1.2	15

41	Chlorine adsorption on the InAs (001) surface. *Semiconductors*, **2011**, 45, 21-29	0.7	7
40	Adsorption of halogen atom (F, Cl, I) on cation-rich GaAs(001) surface. *IOP Conference Series: Materials Science and Engineering*, **2011**, 23, 012015	0.4	5
39	Reconstruction dependence of the etching and passivation of the GaAs(001) surface. *JETP Letters*, **2010**, 91, 466-470	1.2	3
38	Cs-induced charge transfer on (2×4)-GaAs(001) studied by photoemission. *Physical Review B*, **2010**, 81,	3.3	8
37	Oxygen deficiency defects in amorphous Al2O3. *Journal of Applied Physics*, **2010**, 108, 013501	2.5	88
36	Composition and morphology of fluorinated anodic oxides on InAs (1 1 1)A surface. *Applied Surface Science*, **2010**, 256, 5722-5726	6.7	11
35	Preparation of As-rich (2x4) □III-As (001) surfaces by wet chemical treatment and vacuum annealing. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2010**, 7, 264-267		3
34	Reversible superstructural transitions on the GaAs(001) surface under the selective effect of iodine and cesium **2010**, 87, 35		
33	Clean reconstructed InAs(1 1 1) A and B surfaces using chemical treatments and annealing. *Surface Science*, **2009**, 603, 518-522	1.8	14
32	New Ga-enriched reconstructions on the GaAs(001) surface. *JETP Letters*, **2009**, 89, 185-190	1.2	3
31	Electrical properties and deep traps spectra in AlGaN films with nitrogen and gallium polarities prepared by molecular beam epitaxy. *Physica B: Condensed Matter*, **2009**, 404, 4870-4872	2.8	5
30	GaAs(111) A and B surfaces in hydrazine sulfide solutions: Extreme polarity dependence of surface adsorption processes. *Physical Review B*, **2009**, 80,	3.3	6
29	Reversible superstructural transitions on the GaAs(001) surface under the selective effect of iodine and cesium. *JETP Letters*, **2008**, 87, 35-38	1.2	2
28	Energy threshold of Cs-induced chemisorption of oxygen on a GaAs(Cs, O) surface. *JETP Letters*, **2008**, 88, 520-523	1.2	4
27	New reconstruction-stoichiometry correlation for GaAs(001) surface treated by atomic hydrogen. *Applied Surface Science*, **2008**, 254, 8041-8045	6.7	5
26	Soft nitridation of GaAs(100) by hydrazine sulfide solutions: Effect on surface recombination and surface barrier. *Applied Physics Letters*, **2007**, 90, 022104	3.4	25
25	Preparation of Anion - Stabilized III-V Surfaces using Wet Treatments. *Siberian Russian Workshop and Tutorial on Electron Devices and Materials*, **2006**,		1
24	Structure and composition of chemically prepared and vacuum annealed InSb(001) surfaces. *Applied Surface Science*, **2006**, 252, 7684-7690	6.7	19

23	Insulator□metal phase transitions of alkali atoms on GaAs(001). *Surface Science*, **2006**, 600, 287-297	1.8	9
22	Composition and structure of chemically prepared GaAs(1 1 1)A and (1 1 1)B surfaces. *Surface Science*, **2006**, 600, 577-582	1.8	10
21	Chemically prepared well-ordered InP(0 0 1) surfaces. *Surface Science*, **2006**, 600, 3160-3166	1.8	18
20	Cesium-induced surface conversion: From As-rich to Ga-rich GaAs(001) at reduced temperatures. *Physical Review B*, **2005**, 71,	3.3	21
19	Bulklike behavior of the optical anisotropy of cation-rich (001) surfaces of Ga1□InxAs alloys. *Physical Review B*, **2004**, 69,	3.3	3
18	Optical anisotropy induced by cesium adsorption on the As-rich c(2□) reconstruction of GaAs(001). *Physical Review B*, **2004**, 69,	3.3	5
17	Decrease in the bond energy of arsenic atoms on the GaAs(100)-(2□)/c(2□) surface due to the effect of adsorbed cesium. *JETP Letters*, **2004**, 79, 131-135	1.2	20
16	Energy distributions of photoelectrons emitted from p-GaN(Cs, O) with effective negative electron affinity. *JETP Letters*, **2004**, 79, 479-483	1.2	13
15	Low-temperature method of cleaning p-GaN(0001) surfaces for photoemitters with effective negative electron affinity. *Physics of the Solid State*, **2004**, 46, 1949-1953	0.8	32
14	Well-ordered (1 0 0) InAs surfaces using wet chemical treatments. *Surface Science*, **2004**, 570, 237-244	1.8	16
13	Surface passivation and morphology of GaAs(1 0 0) treated in HCl-isopropanol solution. *Applied Surface Science*, **2004**, 235, 249-259	6.7	61
12	Origin of the broadening of surface optical transitions of As-rich and Ga-rich GaAs(0 0 1). *Surface Science*, **2003**, 529, 204-214	1.8	
11	Effect of adsorption of electronegative and electropositive elements on the surface optical anisotropy of GaAs(001). *Physica Status Solidi C: Current Topics in Solid State Physics*, **2003**, 2976-2981		5
10	Surface and bulk origin of the optical anisotropy of As-rich GaAs(001) and Ga1□InxAs(001). *Physical Review B*, **2003**, 67,	3.3	15
9	Preparation of clean reconstructed InAs(001) surfaces using HCl/isopropanol wet treatments. *Applied Physics Letters*, **2003**, 82, 4280-4282	3.4	42
8	Local-order of chemically-prepared GaAs() surfaces. *Surface Science*, **2002**, 507-510, 411-416	1.8	15
7	Structural and electronic transformations at the Cs/GaAs(100) interface. *Surface Science*, **2002**, 507-510, 51-56	1.8	19
6	Evolution of interface excitations under phase transition in two-dimensional layer of Cs on GaAs(1 0 0) and (1 1 1). *Applied Surface Science*, **2001**, 175-176, 175-180	6.7	11

5	Metallicity and disorder at the alkali-metal/GaAs(001) interface. *Physical Review B*, **2001**, 64,	3.3	7
4	Modulated photovoltage changes at the nonmetal–metal transition of the Na/GaAs(001) and K/GaAs(001) interfaces. *Surface Science*, **2001**, 488, 193-206	1.8	
3	Atomic structure and electronic properties of HCl–isopropanol treated and vacuum annealed GaAs(100) surface. *Applied Surface Science*, **1999**, 142, 75-80	6.7	30
2	Cs/GaAs(100) surface: Two-dimensional metal or Hubbard insulator?. *JETP Letters*, **1999**, 70, 550-555	1.2	7
1	Composition and structure of HCl-isopropanol treated and vacuum annealed GaAs(100) surfaces. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1999**, 17, 2655-2662	2.9	86